

60V 3A N-Channel Enhancement Mode Power MOSFET

General Description

This Power MOSFET has been developed using advanced trench process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

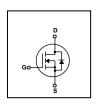
FEATURES

- RDSON \leq 100m Ω @Vgs=10V, Id=3A
- Excellent RDS(ON) and Low Gate Charge

Version: 1.0

· Lead free product is acquired

SYMBOL





SOT-23 top view

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXT1000N06M	SOT-23	Reel

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter		Symbol	Rating	Unit	
		-	SOT-23	<u> </u>	
Drain-Source Voltage	Drain-Source Voltage		V _{DSS}	60	V
Continu		tinuous (T _C = 25°C)		3	Α
Drain Current	Con	tinuous (T _C = 100°C)	ID	2	Α
Drain Current	Drain Current Pulsed (Note1)		I _{DM}	12	Α
Gate-Source Voltage		V_{GSS}	±20	V	
Power Dissipation T _C =25°C		PD	1.5	W	
Maximum Junction Temperature		TJ	150	°C	
Storage Temperature Range		T _{STG}	-55 to 150	°C	

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature



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THERMAL CHARACTERISTICS

Parameter	Symbol	Max.	Unit
Farameter	Symbol	SOT-23	
Thermal Resistance, Junction-to- Ambient	RθJA	83.3	°C/W

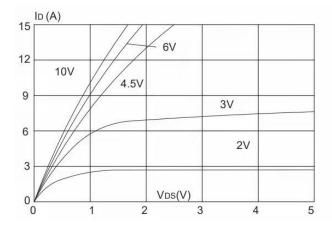
ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250μA	60			V		
Zero Gate Voltage Drain Current	I _{DSS}	VDS=60V, VGS=0V			1	uA		
Gate-Body Leakage Current, Forward	l	VGS=20V			100	nA		
Gate-Body Leakage Current, Reverse	I _{GSS}	VGS=-20V			-100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(TH)}	VDS=VGS, ID=250µA	1	1.5	2.5	V		
	D- even	VGS=10V, ID=3A		85	100	mΩ		
Drain-Source On-State Resistance	R _{DS(ON)}	VGS=4.5V, ID=2A		94	110	mΩ		
DYNAMIC PARAMETERS								
Input Capacitance	Ciss	VDC 25V VCC 0V		325		pF		
Output Capacitance	Coss	VDS=25V, VGS=0V, f=1.0MHz		92		pF		
Reverse Transfer Capacitance	Crss	I=1.0WI1Z		18		pF		
SWITCHING PARAMETERS	SWITCHING PARAMETERS							
Turn-ON Delay Time	t _{D(ON)}			14		ns		
Turn-ON Rise Time	t _R	VDD=30V, ID=2A, VGS =		50		ns		
Turn-OFF Delay Time	t _{D(OFF)}	10V, RG=3Ω		18		ns		
Turn-OFF Fall-Time	t _F			13		ns		
Total Gate Charge(Note2)	Q_{G}	VDS =30V, VGS =10V,		5.2		nC		
Gate Source Charge	Q _{GS}	ID =3A		1.4		nC		
Gate Drain Charge	Q _{GD}	ID =SA		1.6		nC		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage	V _{SD}	IS=3A, VGS=0V			1.2	V		
Diode Continuous Forward Current	Is				3	Α		
Maximum Pulsed Drain to Source Diode Forward Current	Isм				12	А		

Note: 2. Essentially independent of operating temperature



TYPICAL CHARACTERISTICS



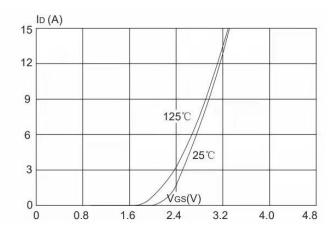
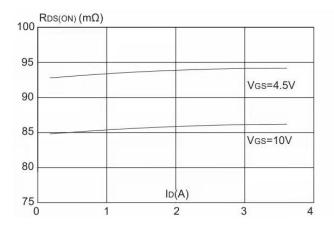


Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics



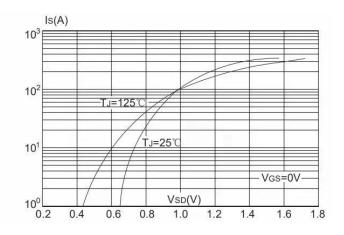
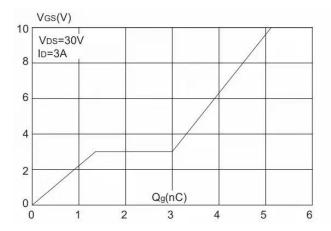


Figure 3:On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics



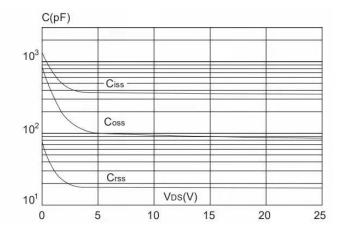


Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics



TYPICAL CHARACTERISTICS(Cont.)

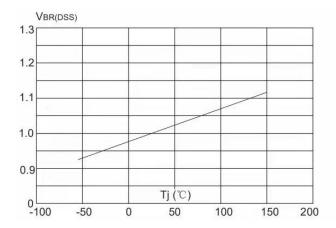


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

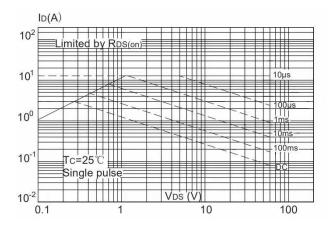


Figure 9: Maximum Safe Operating Area

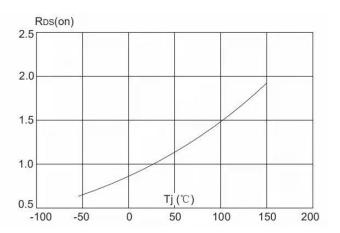


Figure 8: Normalized on Resistance vs. Junction Temperature

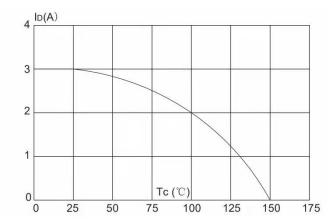
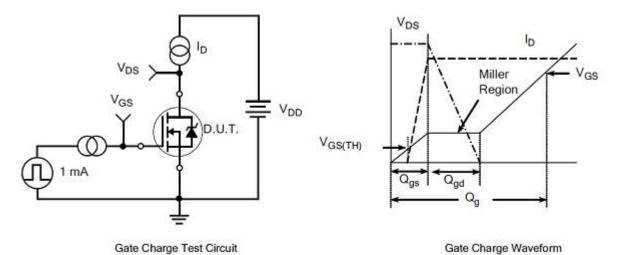


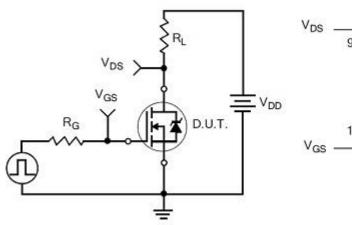
Figure 10: Maximum Continuous Drain Current vs. Case Temperature

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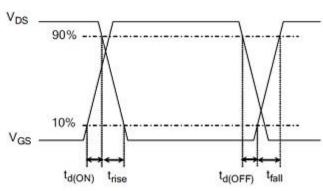


TEST CIRCUITS AND WAVEFORMS







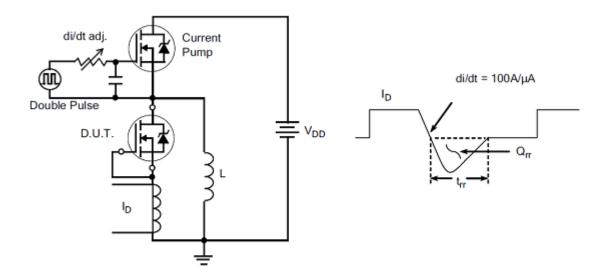


Resistive Switching Waveforms

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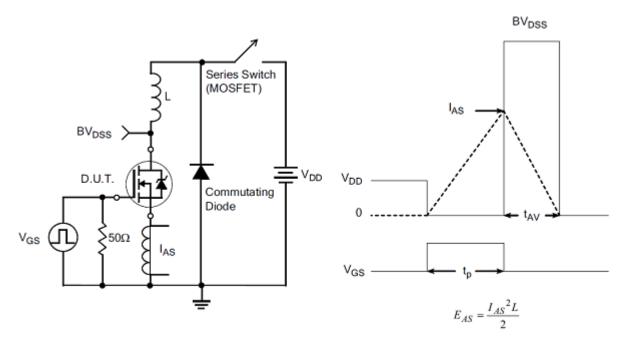


TEST CIRCUITS AND WAVEFORMS(Cont.)



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



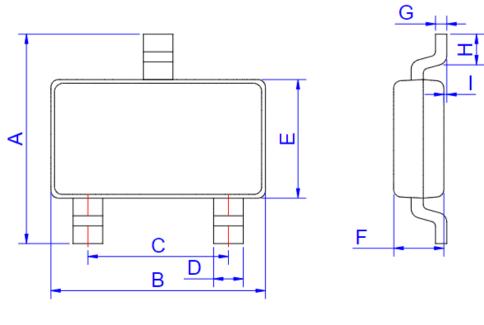
Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

Version: 1.0



SOT-23 Package



SOT-23

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	2.250	2.550	0.089	0.100	
В	2.800	3.000	0.110	0.118	
С	1.800	2.000	0.071	0.079	
D	0.300	0.500	0.012	0.020	
Е	1.200	1.400	0.047	0.055	
F	0.900	1.150	0.035	0.045	
G		0.200		0.008	
Н	0.200		0.008		
1	0.000	0.150	0.000	0.006	



Revision history

Document revision history

Date	Revision	Changes
22-Oct-2020	1.0	First release

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